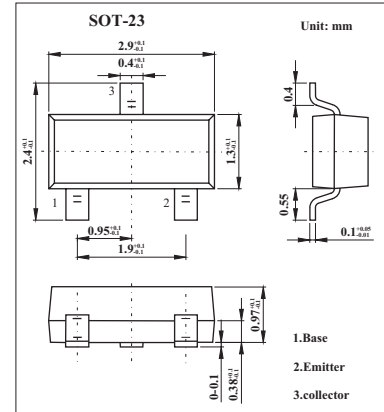


■ Features

- Excellent hFE linearity.
- PNP silicon transistor



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-60	V
Collector-emitter voltage	V <sub>CE0</sub>	-50	V
Emitter-base voltage	V <sub>EB0</sub>	-6	V
Collector current	I <sub>c</sub>	-0.15	A
Collector power dissipation	P <sub>c</sub>	0.2	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> =-50 μ A	-60			V
Collector-emitter breakdown voltage	V <sub>CE0</sub>	I <sub>c</sub> =-1mA	-50			V
Emitter-base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> =-50μA	-6			V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> =-60V			-0.1	μ A
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> =-6V			-0.1	μ A
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> /I <sub>B</sub> =-50mA/-5mA			-0.5	V
DC current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V, I <sub>c</sub> =-1mA	120		560	
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-12V, I <sub>E</sub> =0A, f=1MHz		4.0	5.0	pF
Transition frequency	f <sub>t</sub>	V <sub>CE</sub> =-12V, I <sub>E</sub> =2mA, f=30MHz		140		MHz

■ hFE Classification

Marking	FQ	FR	FS
Rank	Q	R	S
hFE	120~270	180~390	270~560